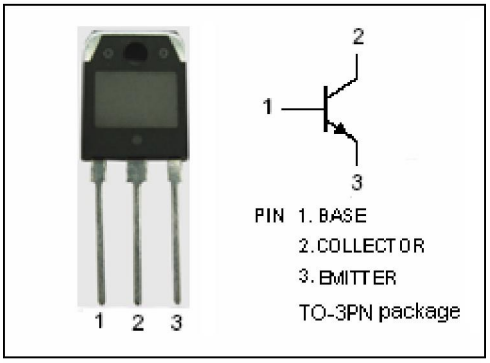
isc Silicon NPN Power Transistor KSC5029



DESCRIPTION

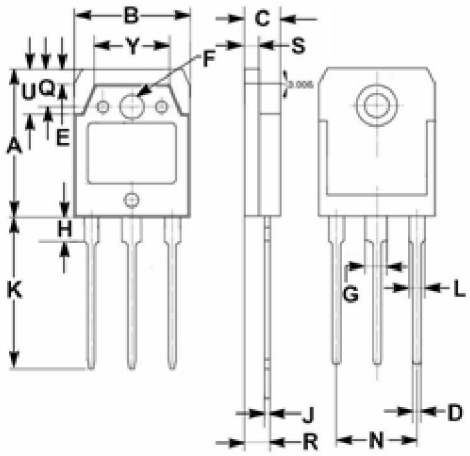
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 800V(Min)
- High Switching Speed
- Wide Area of Safe Operation

APPLICATIONS

- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4.5	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ T_C=25℃	90	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEX(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 2A ;I_{B1}= -I_{B2}= 0.4A; L= 2mH,Clamped	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	1100			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 5mA; R_{BE}= ∞	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.4A			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 0.4A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0			10	μA
h_{FE-1}	DC Current Gain	I_C= 0.3A; V_{CE}= 5V	10		40	
h_{FE-2}	DC Current Gain	I_C= 1.5A; V_{CE}= 5V	8			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1MHz		90		pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.3A ; V_{CE}= 10V		15		MHz
Switching Times; Resistive Load						
t_{on}	Turn-On Time	I_C= 3A; I_{B1}= 0.6A; I_{B2}= -1.2A; V_{CC}= 400V; R_L= 133Ω			0.5	μs
t_s	Storage Time				3.0	μs
t_f	Fall Time				0.3	μs

◆ **h_{FE-1} Classifications**

N	R	O
10-20	15-30	20-40